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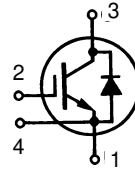
# High Voltage IGBT with Diode

## IXSN 35N120AU1

$$V_{CES} = 1200 \text{ V}$$

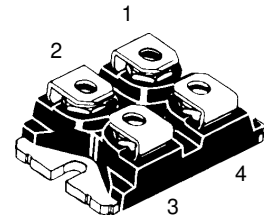
$$I_{C25} = 70 \text{ A}$$

$$V_{CE(sat)} = 4 \text{ V}$$



Symbol	Test Conditions	Maximum Ratings	
$V_{CES}$	$T_J = 25^\circ\text{C}$ to $150^\circ\text{C}$	1200	V
$V_{CGR}$	$T_J = 25^\circ\text{C}$ to $150^\circ\text{C}$ ; $R_{GE} = 1 \text{ M}\Omega$	1200	A
$V_{GES}$	Continuous	$\pm 20$	V
$V_{GEM}$	Transient	$\pm 30$	V
$I_{C25}$	$T_C = 25^\circ\text{C}$	70	A
$I_{C90}$	$T_C = 90^\circ\text{C}$	35	A
$I_{CM}$	$T_C = 25^\circ\text{C}$ , 1 ms	140	A
<b>SSOA (RBSOA)</b>	$V_{GE} = 15 \text{ V}$ , $T_{VJ} = 125^\circ\text{C}$ , $R_G = 22 \Omega$ Clamped inductive load, $L = 30 \mu\text{H}$	$I_{CM} = 70$ @ $0.8 V_{CES}$	A
<b><math>t_{SC}</math> (SCSOA)</b>	$V_{GE} = 15 \text{ V}$ , $V_{CE} = 0.6 \cdot V_{CES}$ , $T_J = 125^\circ\text{C}$ $R_G = 22 \Omega$ , non repetitive	10	$\mu\text{s}$
$P_C$	$T_C = 25^\circ\text{C}$	300	W
$P_D$		175	W
$V_{ISOL}$	50/60 Hz $I_{ISOL} \leq 1 \text{ mA}$	$t = 1 \text{ min}$	2500 V~
		$t = 1 \text{ s}$	3000 V~
$T_J$		-55 ... +150	$^\circ\text{C}$
$T_{JM}$		150	$^\circ\text{C}$
$T_{stg}$		-55 ... +150	$^\circ\text{C}$
$M_d$	Mounting torque	1.5/13	Nm/lb.in.
	Terminal connection torque (M4)	1.5/13	Nm/lb.in.
<b>Weight</b>		30	g

miniBLOC, SOT-227 B



1 = Emitter ①, 3 = Collector  
2 = Gate, 4 = Emitter ①

① Either Emitter terminal can be used as Main or Kelvin Emitter

### Features

- International standard package miniBLOC (ISOTOP) compatible
- Aluminium-nitride isolation
  - high power dissipation
- Isolation voltage 3000 V~
- Low  $V_{CE(sat)}$ 
  - for minimum on-state conduction losses
- Fast Recovery Epitaxial Diode
  - short  $t_{rr}$  and  $I_{RM}$
- Low collector-to-case capacitance (< 50 pF)
  - reduces RFI
- Low package inductance (< 10 nH)
  - easy to drive and to protect

### Applications

- AC motor speed control
- DC servo and robot drives
- DC choppers
- Uninterruptible power supplies (UPS)
- Switch-mode and resonant-mode power supplies

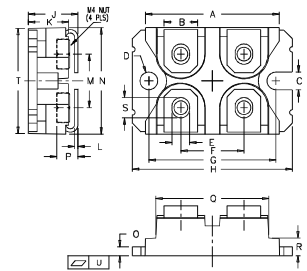
### Advantages

- Space savings
- Easy to mount with 2 screws
- High power density

Symbol	Test Conditions	Characteristic Values ( $T_J = 25^\circ\text{C}$ , unless otherwise specified)		
		min.	typ.	max.
$BV_{CES}$	$I_C = 5 \text{ mA}$ , $V_{GE} = 0 \text{ V}$	1200		V
$V_{GE(th)}$	$I_C = 4 \text{ mA}$ , $V_{CE} = V_{GE}$	4		V
$I_{CES}$ ①	$V_{CE} = 0.8 \cdot V_{CES}$ $V_{GE} = 0 \text{ V}$			750 $\mu\text{A}$ 15 mA
$I_{GES}$	$V_{CE} = 0 \text{ V}$ , $V_{GE} = \pm 20 \text{ V}$			$\pm 100 \text{ nA}$
$V_{CE(sat)}$	$I_C = I_{C90}$ , $V_{GE} = 15 \text{ V}$			4 V

② Device must be heat sunk during high temperature leakage test to avoid thermal runaway.

Symbol	Test Conditions	Characteristic Values ( $T_J = 25^\circ\text{C}$ , unless otherwise specified)		
		min.	typ.	max.
$g_{fs}$	$I_C = I_{C90}$ ; $V_{CE} = 10\text{ V}$ , Pulse test, $t \leq 300\ \mu\text{s}$ , duty cycle $d \leq 2\%$	20	26	S
$I_{C(on)}$	$V_{CE} = 10\text{ V}$ , $V_{GE} = 15\text{ V}$		170	A
$C_{ies}$	$V_{CE} = 25\text{ V}$ , $V_{GE} = 0\text{ V}$ , $f = 1\text{ MHz}$		3900	pF
$C_{oes}$			295	pF
$C_{res}$			60	pF
$Q_g$	$I_C = I_{C90}$ , $V_{GE} = 15\text{ V}$ , $V_{CE} = 0.5 V_{CES}$		150	190 nC
$Q_{ge}$			40	60 nC
$Q_{gc}$			70	100 nC
$t_{d(on)}$	<b>Inductive load, <math>T_J = 25^\circ\text{C}</math></b> $I_C = I_{C90}$ , $V_{GE} = 15\text{ V}$ , $V_{CE} = 0.8 \cdot V_{CES}$ , $R_G = 2.7\ \Omega$ Remarks: Switching times may increase for $V_{CE}(\text{Clamp}) > 0.8 \cdot V_{CES}$ , higher $T_J$ or increased $R_G$		80	ns
$t_{ri}$			150	ns
$t_{d(off)}$			400	900 ns
$t_{fi}$			500	700 ns
$E_{off}$			10	mJ
$t_{d(on)}$	<b>Inductive load, <math>T_J = 125^\circ\text{C}</math></b> $I_C = I_{C90}$ , $V_{GE} = 15\text{ V}$ , $V_{CE} = 0.8 \cdot V_{CES}$ , $R_G = 2.7\ \Omega$ Remarks: Switching times may increase for $V_{CE}(\text{Clamp}) > 0.8 \cdot V_{CES}$ , higher $T_J$ or increased $R_G$		80	ns
$t_{ri}$			150	ns
$t_{d(off)}$			400	ns
$t_{fi}$			700	ns
$E_{on}$			6	mJ
$E_{off}$		15	mJ	
$R_{thJC}$				0.42 K/W
$R_{thCK}$		0.05		K/W

**miniBLOC, SOT-227 B**


M4 screws (4x) supplied

Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	31.50	31.88	1.240	1.255
B	7.80	8.20	0.307	0.323
C	4.09	4.29	0.161	0.169
D	4.09	4.29	0.161	0.169
E	4.09	4.29	0.161	0.169
F	14.91	15.11	0.587	0.595
G	30.12	30.30	1.186	1.193
H	38.00	38.23	1.496	1.505
J	11.68	12.22	0.460	0.481
K	8.92	9.60	0.351	0.378
L	0.76	0.84	0.030	0.033
M	12.60	12.85	0.496	0.506
N	25.15	25.42	0.990	1.001
O	1.98	2.13	0.078	0.084
P	4.95	5.97	0.195	0.235
Q	26.54	26.90	1.045	1.059
R	3.94	4.42	0.155	0.174
S	4.72	4.85	0.186	0.191
T	24.59	25.07	0.968	0.987
U	-0.05	0.1	-0.002	0.004

Symbol	Test Conditions	Characteristic Values ( $T_J = 25^\circ\text{C}$ , unless otherwise specified)		
		min.	typ.	max.
$V_F$	$I_F = I_{C90}$ , $V_{GE} = 0\text{ V}$ , Pulse test, $t \leq 300\ \mu\text{s}$ , duty cycle $d \leq 2\%$			2.35 V
$I_{RM}$	$I_F = I_{C90}$ , $V_{GE} = 0\text{ V}$ , $-di_F/dt = 480\text{ A}/\mu\text{s}$ $V_R = 540\text{ V}$ $T_J = 100^\circ\text{C}$ $I_F = 1\text{ A}$ ; $-di/dt = 200\text{ A}/\mu\text{s}$ ; $V_R = 30\text{ V}$ $T_J = 25^\circ\text{C}$		32	35 A
$t_{rr}$			225	ns
			40	60 ns
$R_{thJC}$				0.71 K/W

Fig. 1 Saturation Characteristics

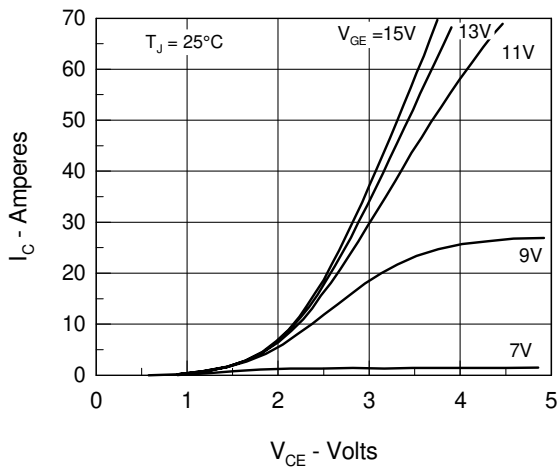


Fig. 2 Output Characteristics

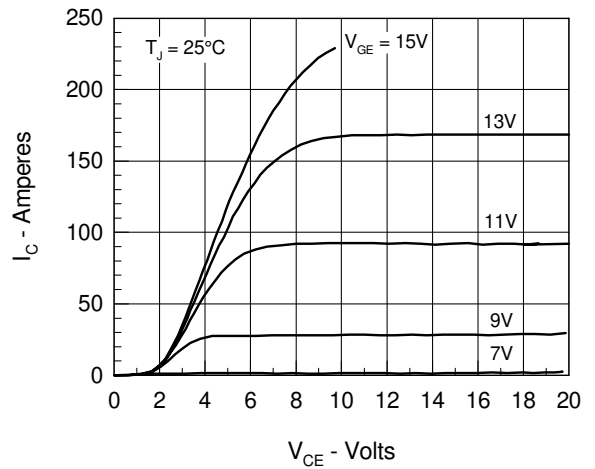


Fig. 3 Collector-Emitter Voltage vs. Gate-Emitter Voltage

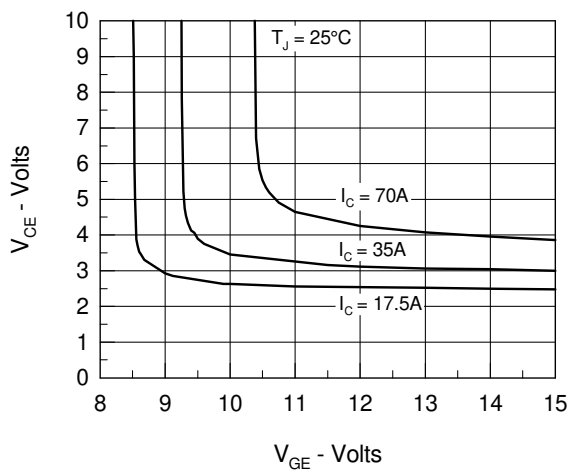


Fig. 4 Temperature Dependence of Output Saturation Voltage

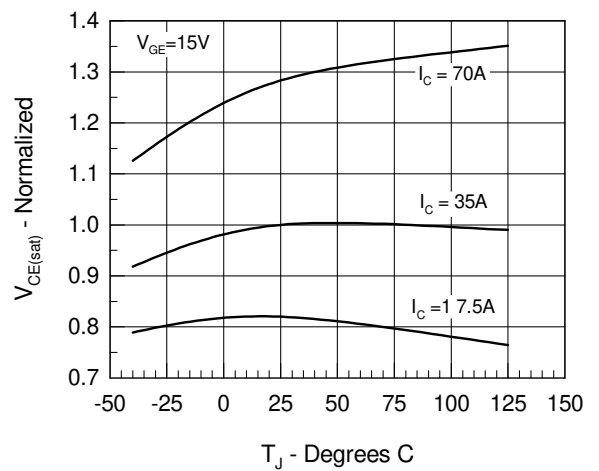


Fig. 5 Input Admittance

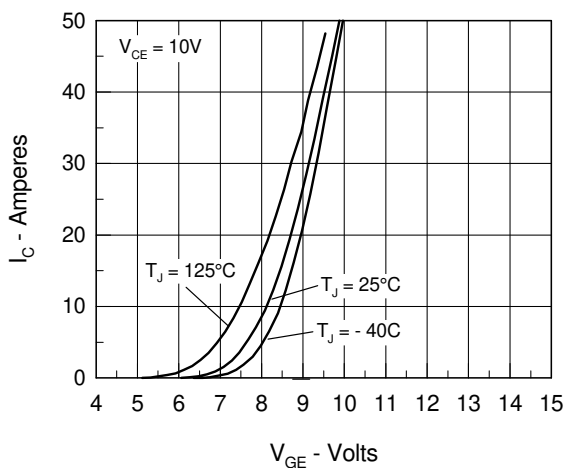
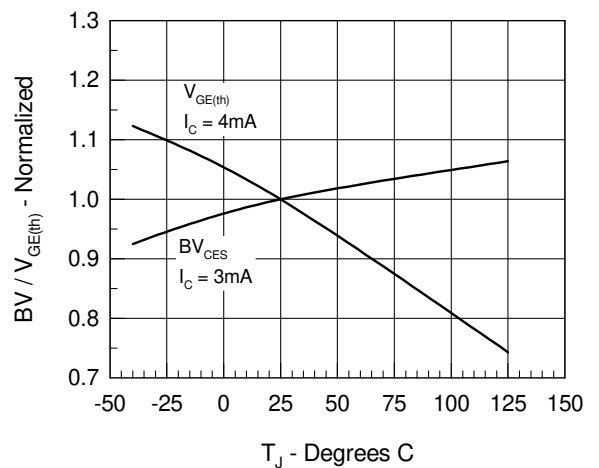
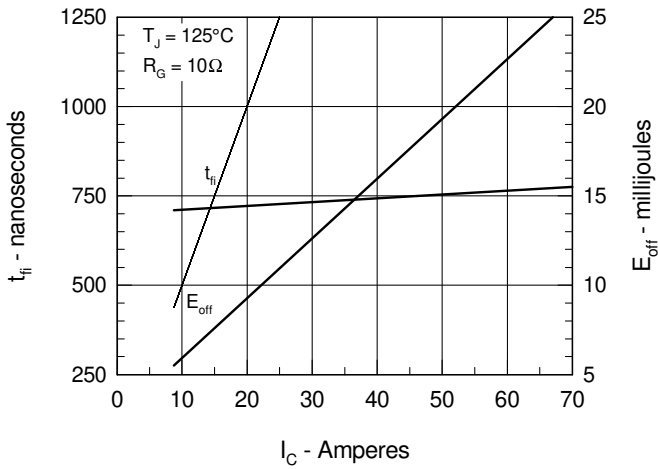


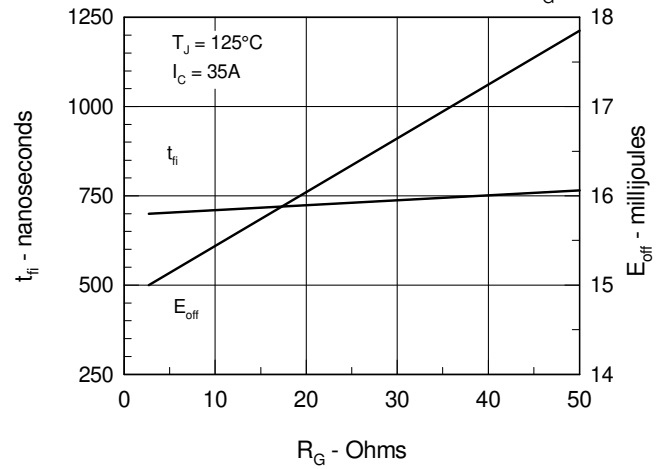
Fig. 6 Temperature Dependence of Breakdown and Threshold Voltage



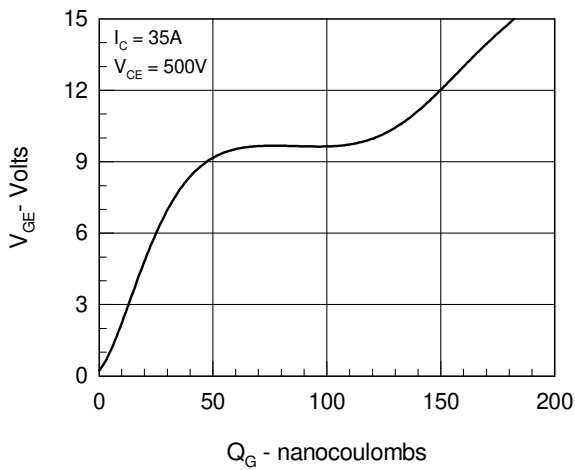
**Fig.7 Turn-Off Energy per Pulse and Fall Time on Collector Current**



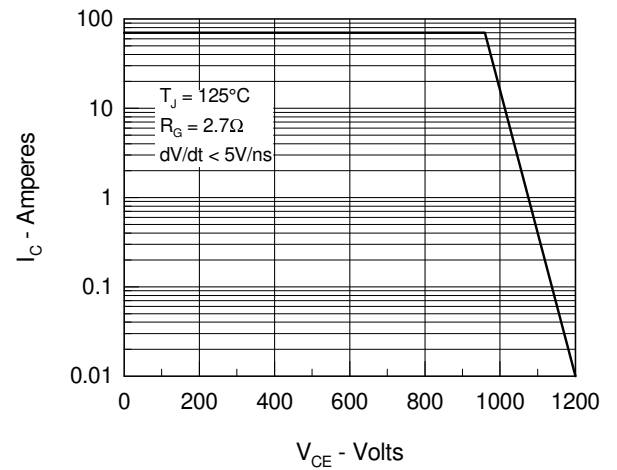
**Fig.8 Dependence of Turn-Off Energy Per Pulse and Fall Time on  $R_G$**



**Fig.9 Gate Charge Characteristic Curve**



**Fig.10 Turn-Off Safe Operating Area**



**Fig.11 Transient Thermal Impedance**

